

**SMD Type Phototransistor with Daylight Filter****Features**

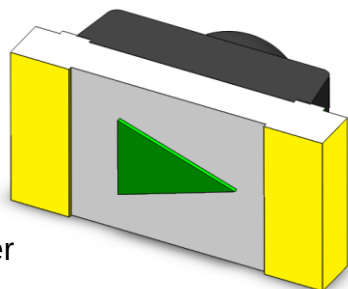
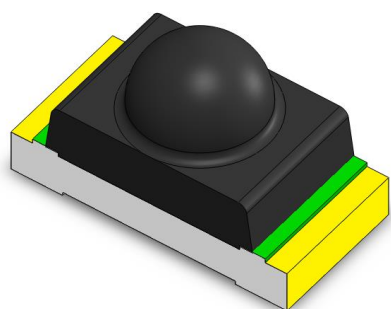
- Small double-end package
- High photo sensitivity
- High reliability
- Spectral range of sensitivity: 760-1100nm
- Fast Response time
- RoHS compliance

Applications

- Infrared sensor
- Infrared Touch Panel Solutions

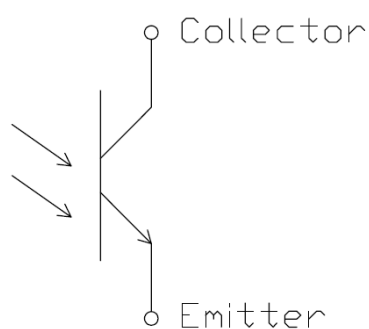
Description

The PTP81608BT09 is silicon NPN Phototransistor housed in a miniature SMD package. The device comes with a superior filtering for visible light by utilizing special black molding compound.

Package Outline

Emitter

Collector

Schematic



SMD Type Phototransistor with Daylight Filter

Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
I _C	Collector Current	20	mA	
B _V CEO	Collector-Emitter Voltage	35	V	1
B _V ECO	Emitter-Collector Voltage	5	V	2
T _{opr}	Operating Temperature	-40 ~ +85	°C	
T _{stg}	Storage Temperature	-40 ~ +100	°C	
T _{sol}	Soldering Temperature	260	°C	3
P _{to}	Total Power Dissipation	150	mW	

Optical Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
λ	Spectral Bandwidth	-	760	-	1100	nm	
λ _P	Peak Sensitivity	-	-	880	-	nm	
θ1/2	View Angle	V _{CE} =5V	-	±40	-	deg	

Electrical Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
I _{CEO}	Dark Current	Ee=0mW /cm ² V _{CE} =20V	-	-	100	nA	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	Ee=1mW /cm ² I _C =0.9mA	-	-	0.4	V	
I _C	Collector Light Current	Ee=1mW /cm ² λ _P =940nm, V _{CE} =5V	0.9	1.8	-	mA	
C _T	Terminal Capacitance	Ee=0mW /cm ² f=1MHz, V _{CE} =5V	-	3.80	-	pF	



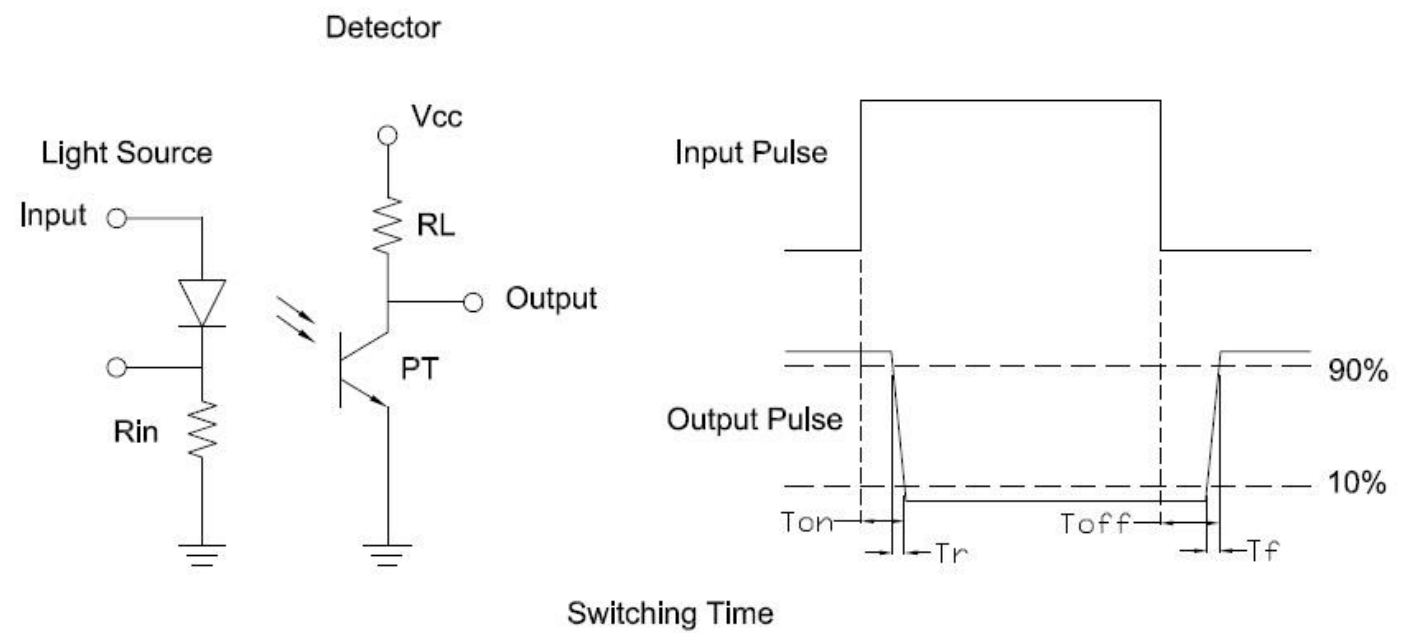
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Switching Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
t_r	Rise Time	$V_{ce} = 5V, R_L = 100\Omega$ $I_C = 1.0mA$	-	6	-	μs	4
t_f	Fall Time		-	7	-		
t_{on}	Turn on Delay Time		-	11	-		
t_{off}	Turn off Delay Time		-	7.9	-		

Notes:

- 1 : Test conditions : $I_C = 100\mu A, E_e = 0mW/cm^2$.
- 2 : Test conditions : $I_E = 100\mu A, E_e = 0mW/cm^2$.
- 3 : Soldering time ≤ 5 seconds.
- 4 : Test circuit:





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Typical Characteristic Curves

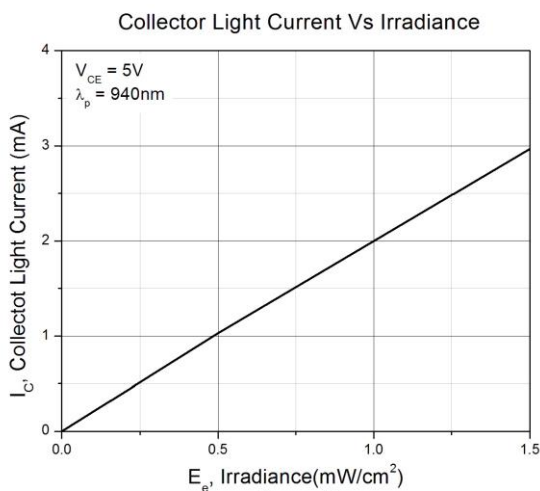


Figure 1

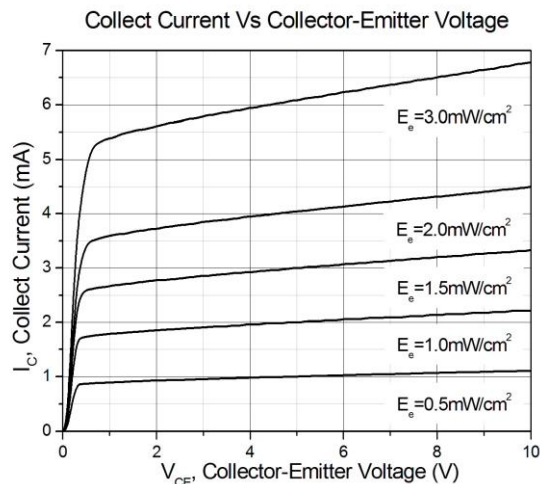


Figure 2

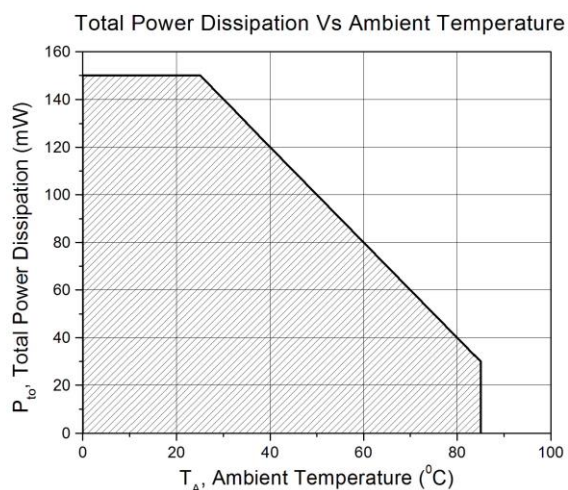


Figure 3

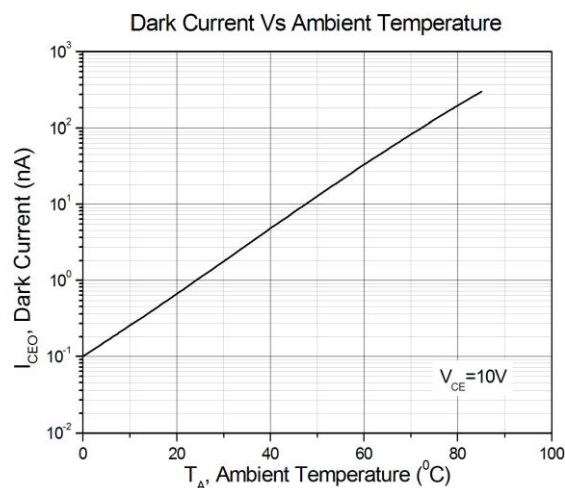


Figure 4

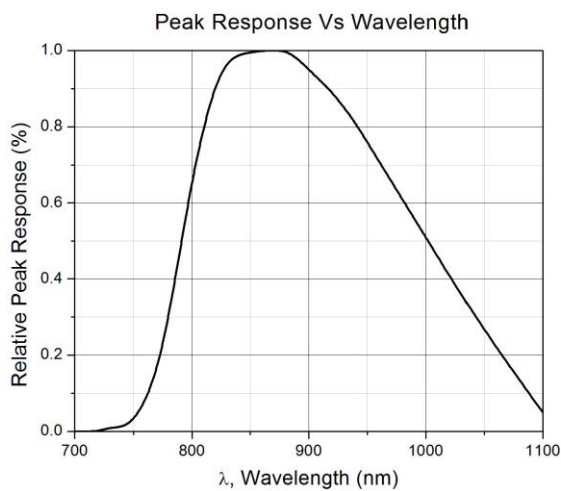


Figure 5

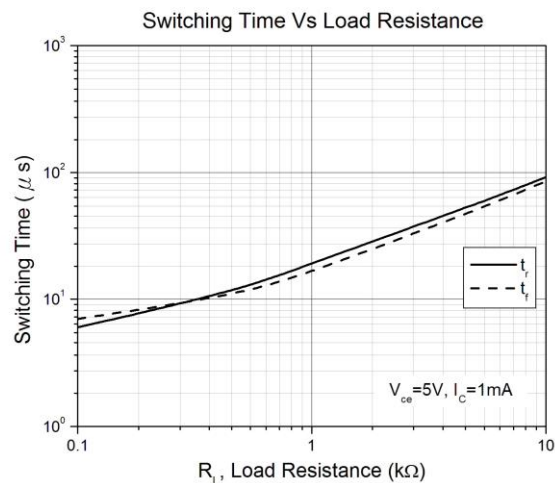
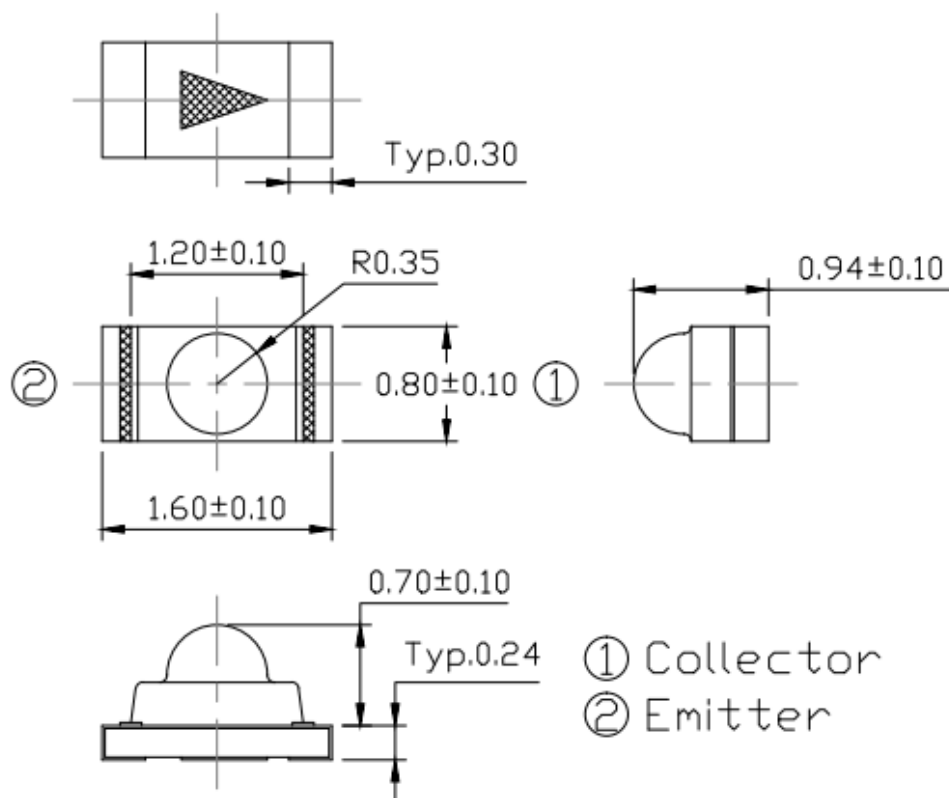


Figure 6

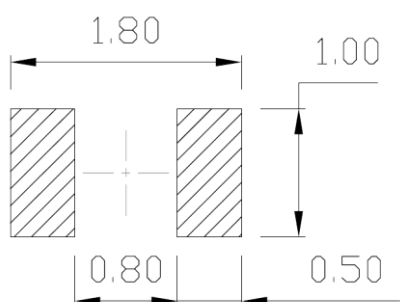


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Package Dimension *All dimensions are in mm, unless otherwise stated*



Recommended Soldering Mask *All dimensions are in mm, unless otherwise stated*

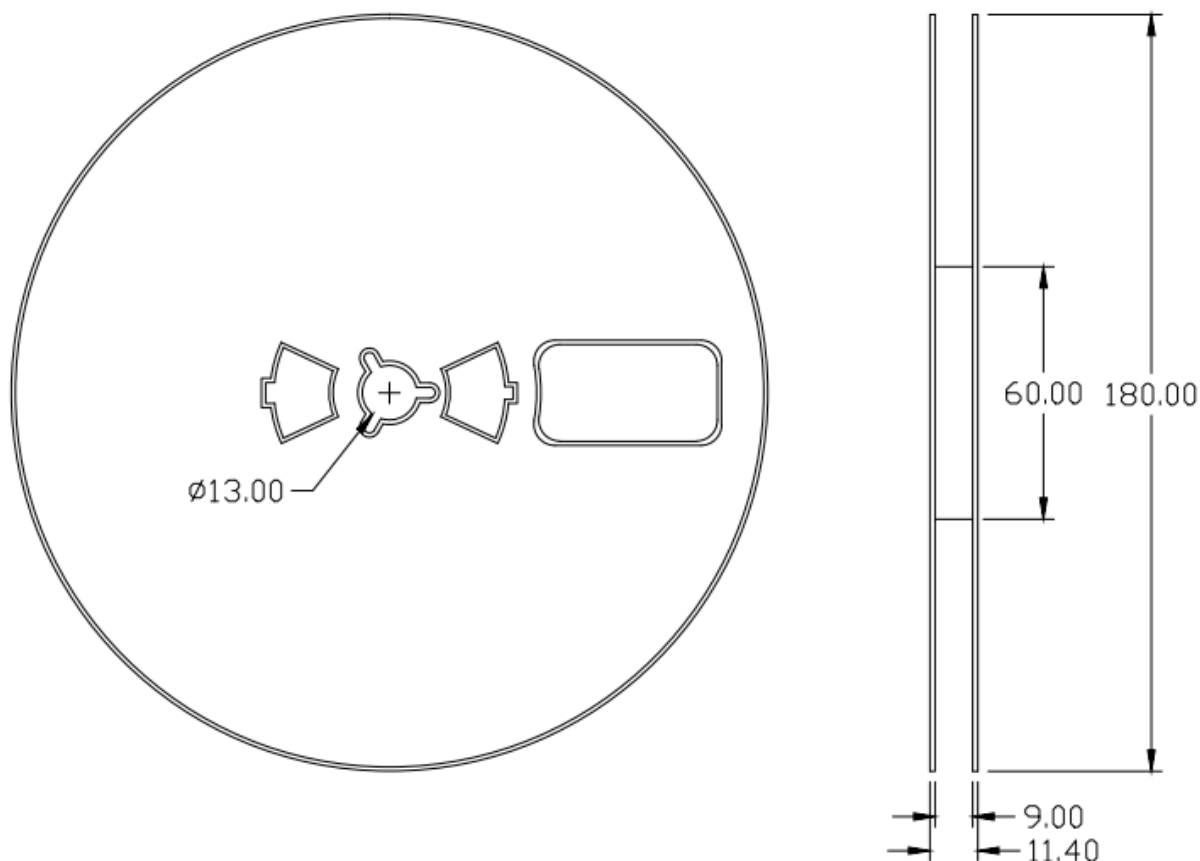
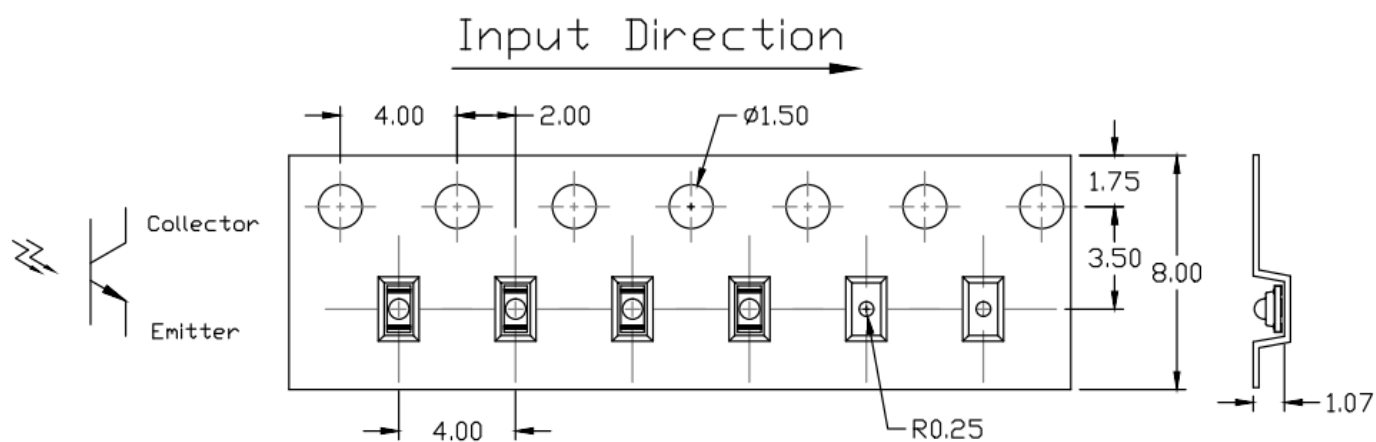


Ordering Information

Part Number	Description	Quantity
PTP81608BT09	Tape & Reel	4000 pcs



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Reel Dimension *All dimensions are in mm, unless otherwise stated***Tape Dimension** *All dimensions are in mm, unless otherwise stated*



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Label Form Specification

CT Micro
International Corporation

MADE IN CHINA

Part no.: XXXXXXXXX
Serial no.: XX000XX
Lot no.: XXXXXXXXX
Q'ty: XXXX pcs
Date Code: 20XXXXX

Bin Code: X

RoHS
Pb-free

Part no: CTM Production Number
Serial no: Production Number
Lot no: Lot number
Q'ty: Packing Quantity
Date Code: Manufacture Date
Bin Code: Ic Ranks
MADE IN CHINA: Production Place

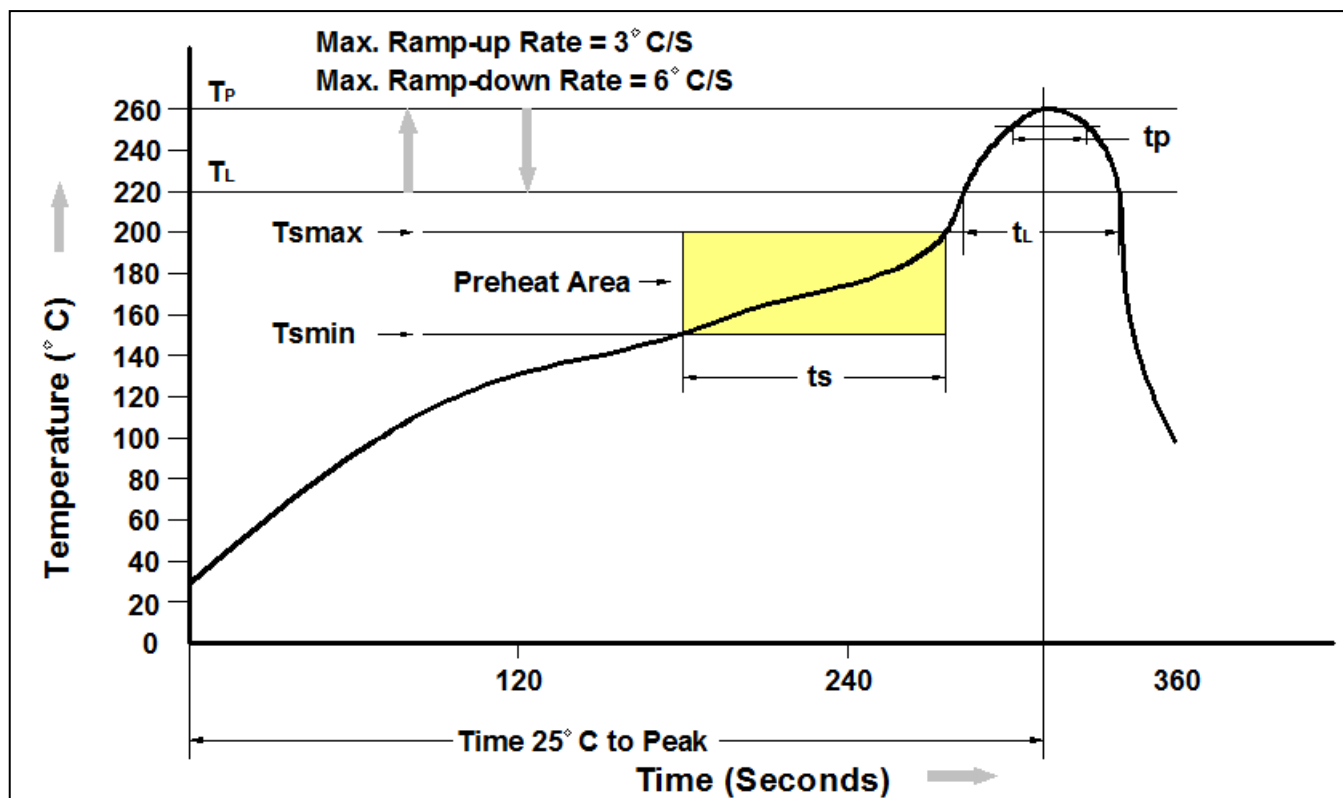
Storage Condition

1. Do not open moisture proof bag before the products are ready to use.
2. The moisture barrier bag should be stored at 30°C and 90%R.H. max. before opening.
Shelf life of non-opened bag is 12 months after the bag sealing date.
3. After opening the moisture barrier bag floor life is 168h at 30°C/60%RH. max. Unused LEDs should be resealed into moisture barrier bag. (Refer to J-STD-020 Standard)
4. If the moisture absorbent material has faded away or the LEDs have exceeded the storage time, baking treatment should be performed using the J-STD-033 Standard conditions.



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Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of 260°C	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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